



Billion-year Ultradense Memory

Will Gannett

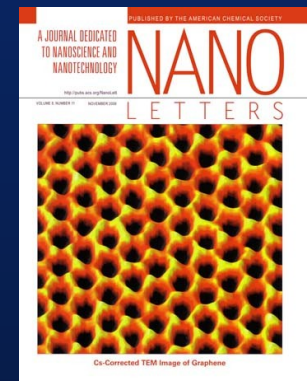
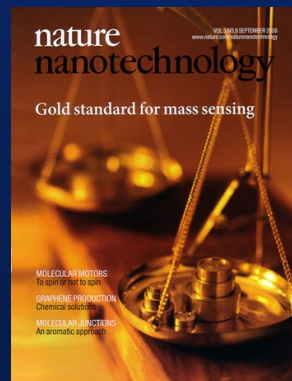
Prof. Alex Zettl

Physics Dept, UC Berkeley

Lawrence Berkeley National Lab

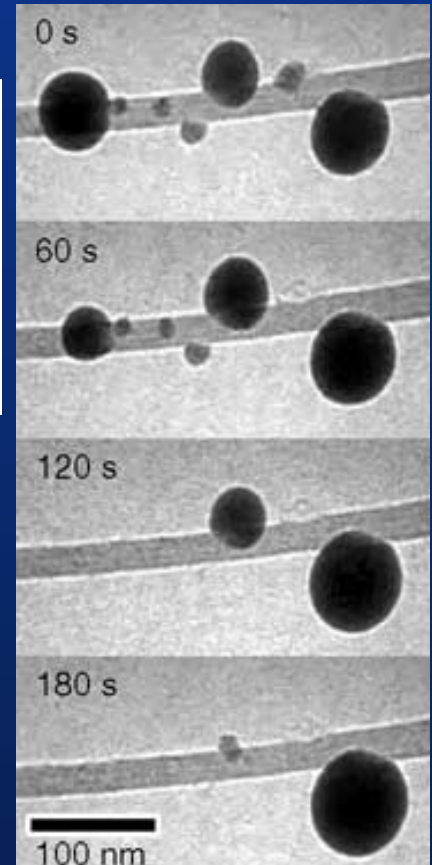


- Synthesis and characterization of novel nanomaterials
Graphene, h-BN, nanotubes
- Nano-electromechanical systems (NEMS)
Graphene/CNT resonators, rotors



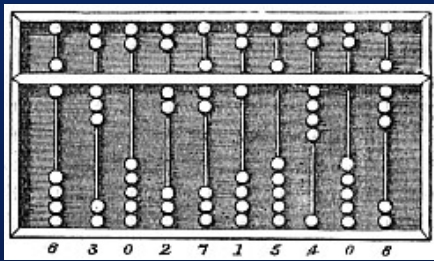
Material Properties Used for Data

Charge density	NAND flash
Ferromagnetic orientation	Tape, HDD
Crystalline phase	PCM

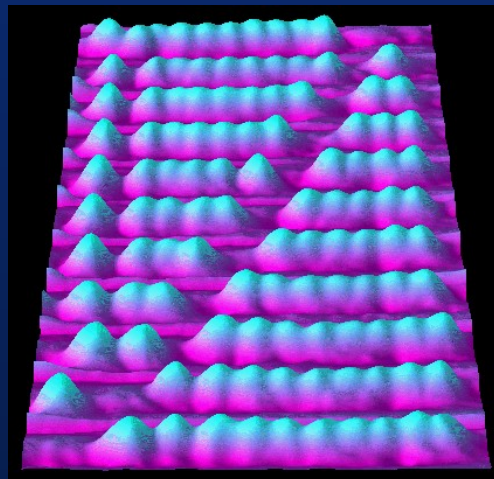


B.C. Regan, A. Zettl *et al.*,
Nature **428**, 924 (2004)

■ Position?

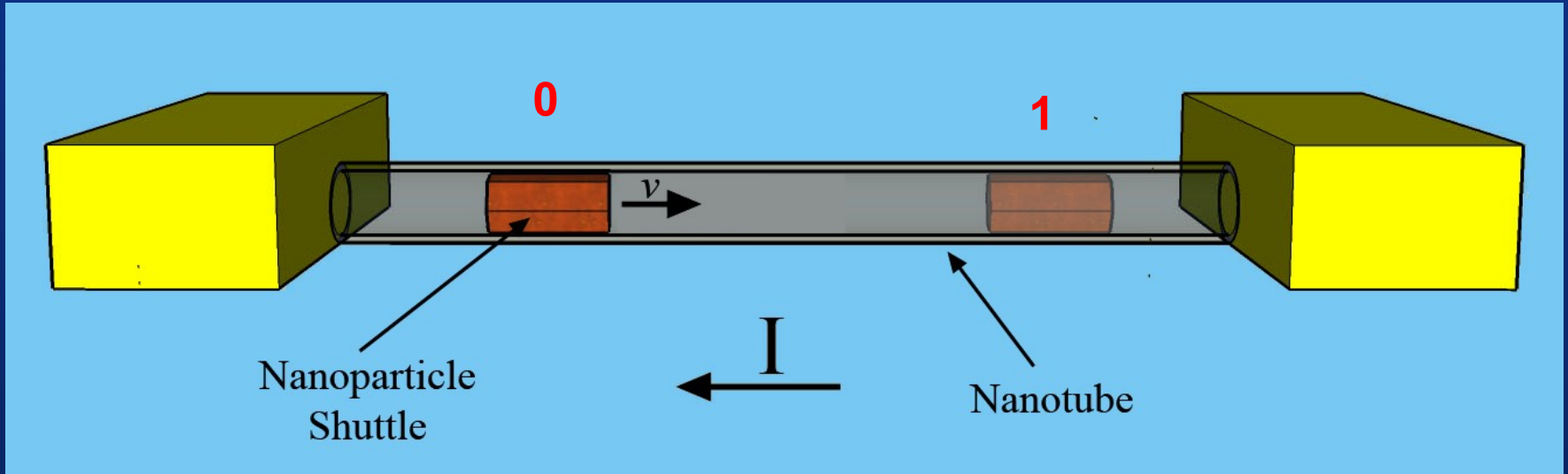


http://commons.wikimedia.org/wiki/File:Abacus_6.png



M. T. Cuberes, R. R. Schlittler, and J. K. Gimzewski
Appl. Phys. Lett. **69**, 3016 (1996). (IBM Zurich)
<http://www.research.ibm.com/atomic/nano/abacus.gif>

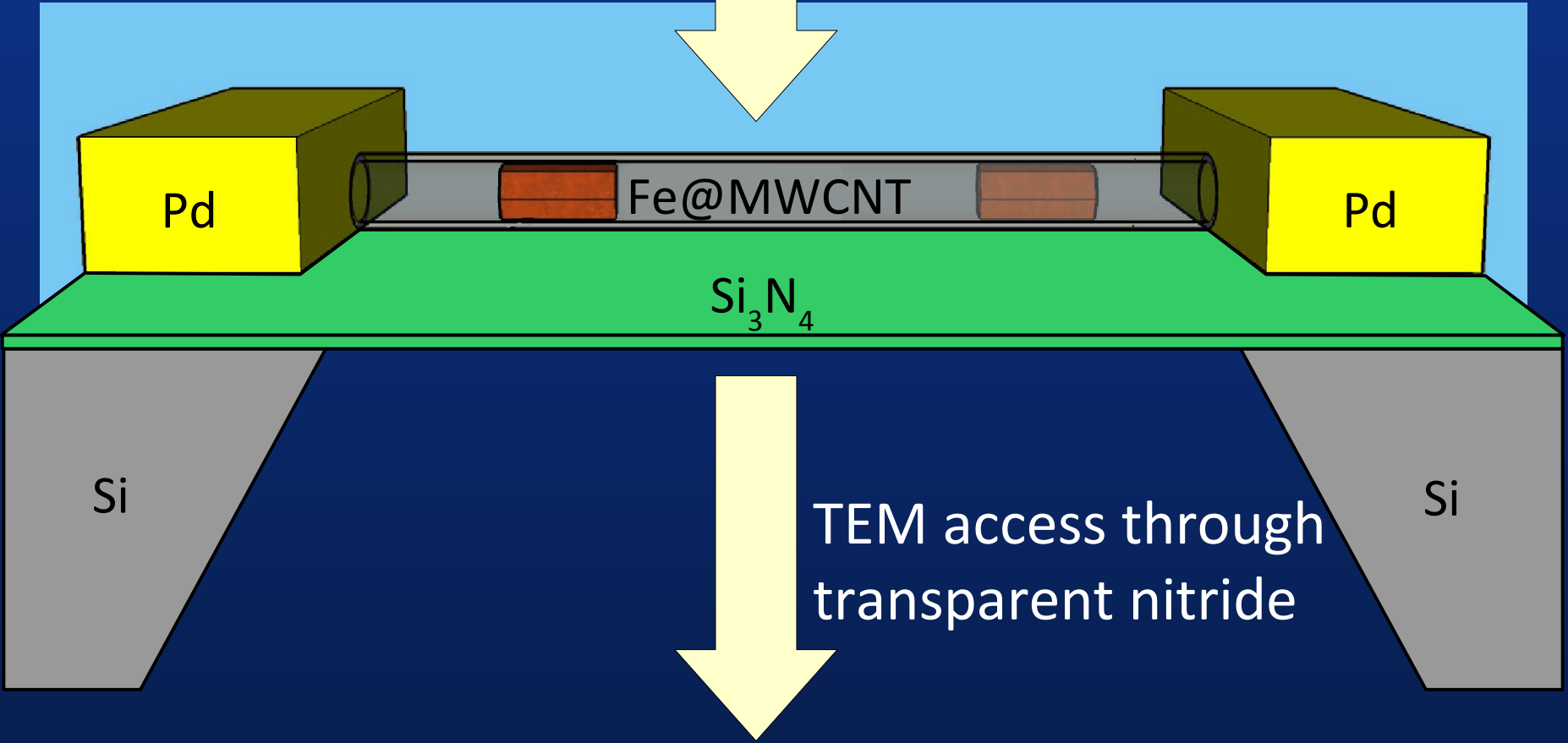
Proposed Nanomechanical Memory



G.E. Begtrup, W. Gannett, T. D. Yuzvinsky, V. H. Crespi and A. Zettl. Nanoscale reversible mass transport for archival memory. *Nano Letters* **9** (5), 1835-1838 (2009).

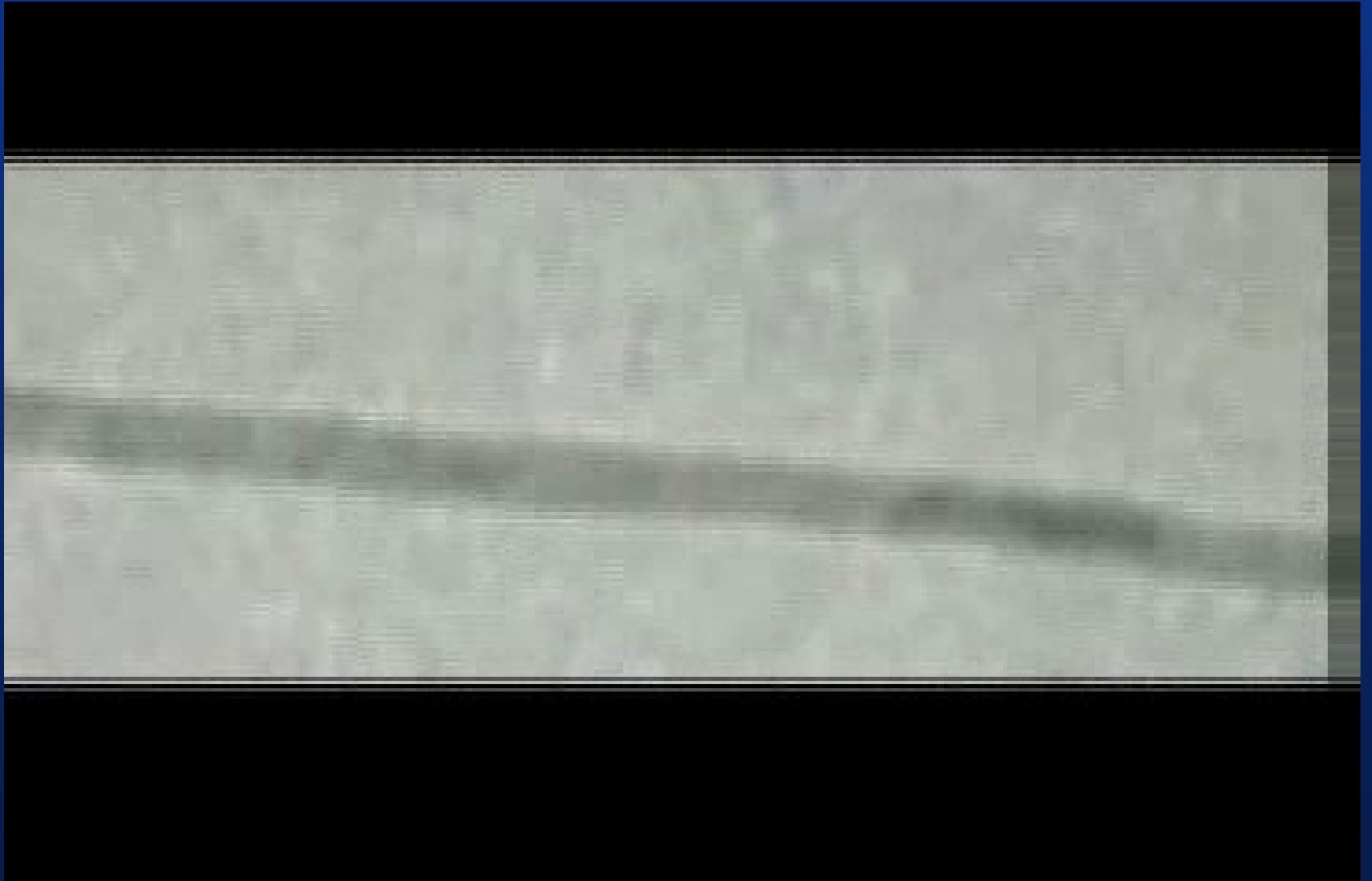
- Nanoparticle slides within carbon nanotube
- Nanotube protects particle from environment

Device as Fabricated

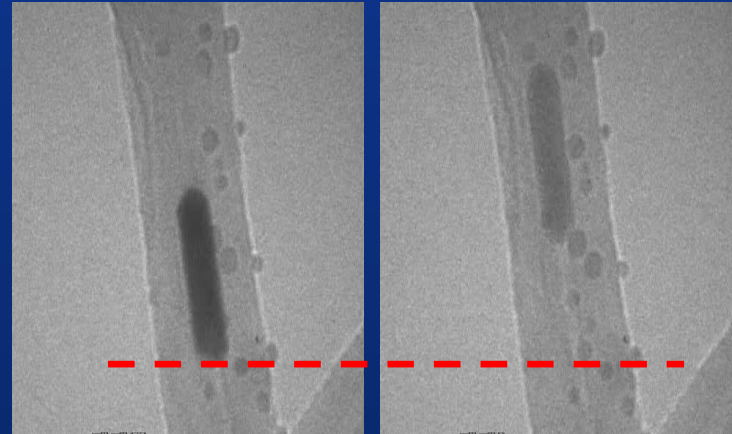
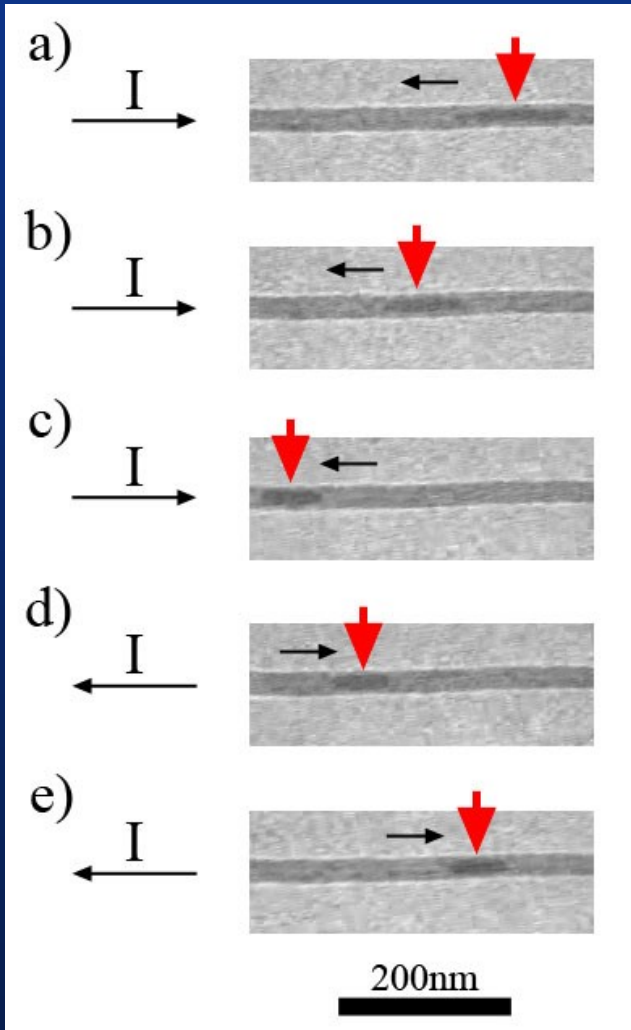




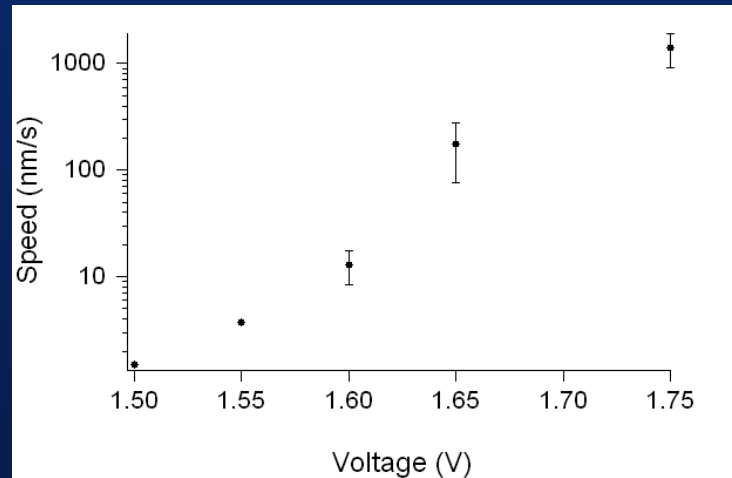
Writing and Rewriting



Nanocrystal Movement



Max observed velocity: $>25 \mu\text{m}/\text{sec}$





How to read out?

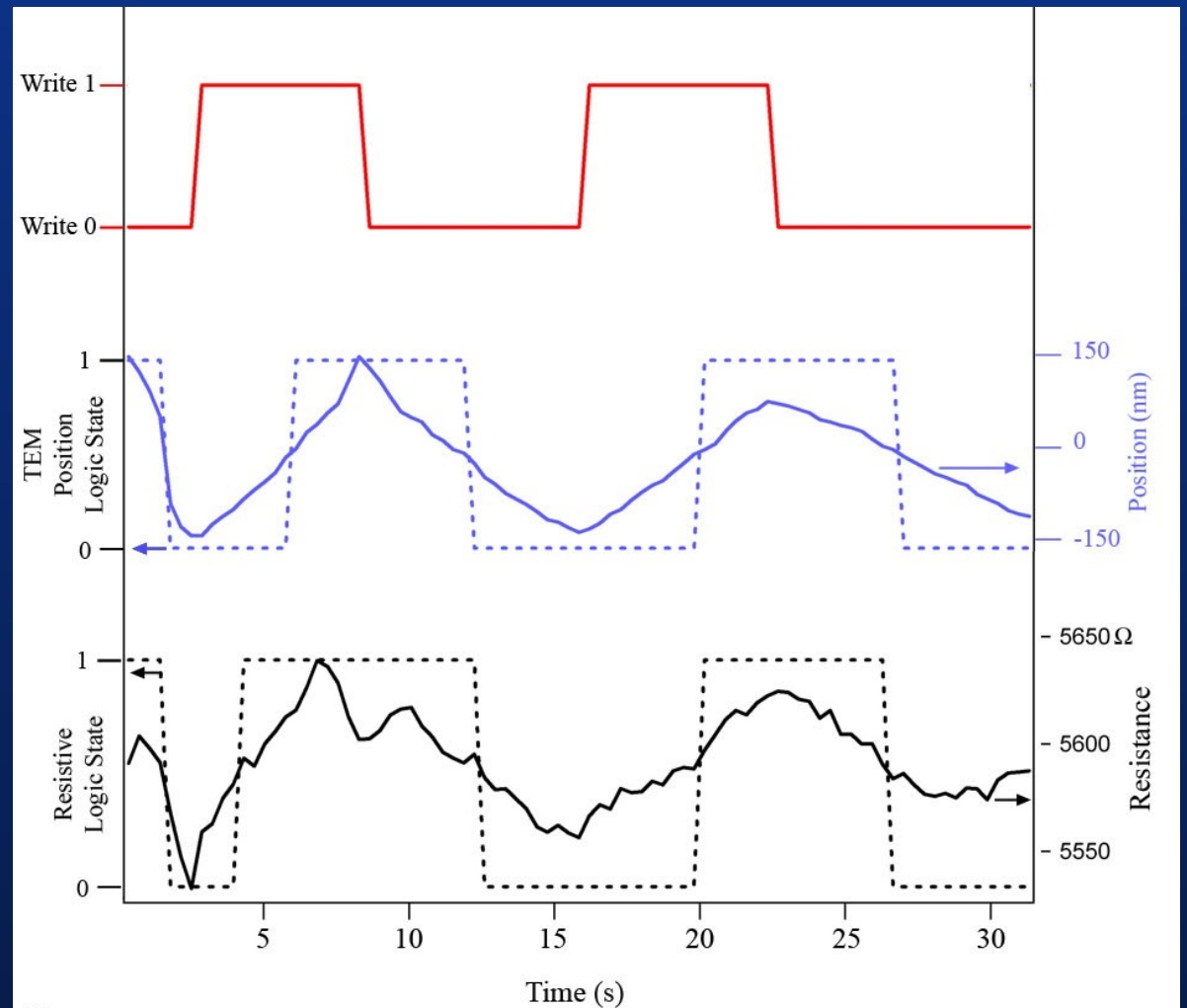
- TEM
- Scanning probe (STM)
 - Far too bulky/costly
- Asymmetric gate
 - Better, but still 3-wire
- Would like a simple “in-line” measurement
 - 2-probe...what about resistance?

Write and Read - Timeseries

Write signal

TEM observation
Read-out

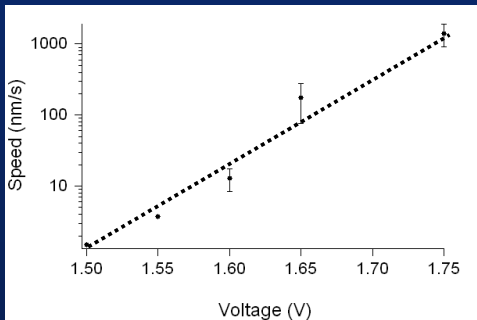
Resistance
Read-out



- Modeled as sawtooth potential of height ΔE

$$v \sim \omega L e^{-\left(\Delta E - \frac{1}{2} Q_{eff} V \frac{L}{D}\right) / k_B T}$$

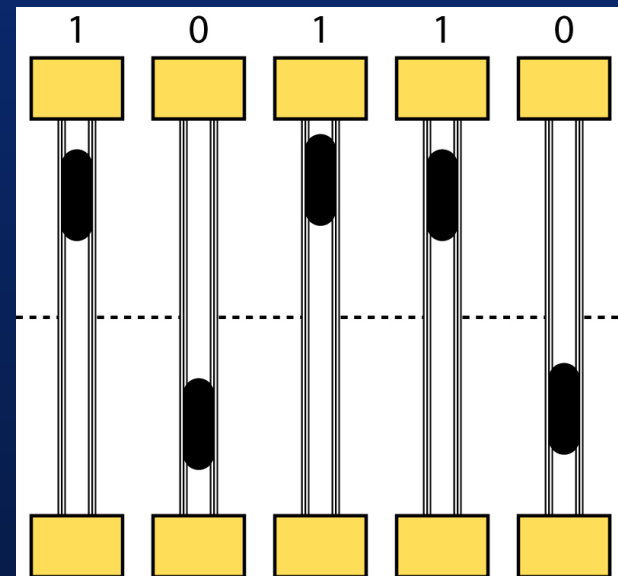
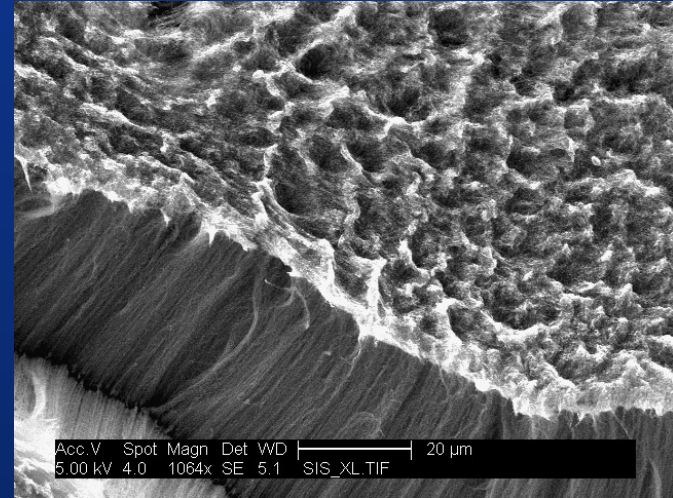
- Speed vs voltage data $\rightarrow \Delta E \sim 1.5-1.7$ eV



- Estimated dwell time of $>10^9$ years at 300K

Arrays of devices?

- Growth of CNT forests
- How to address individual devices?
- Density:
5 nm x 100 nm / bit
→ 1 Tbit/in²





Future directions for Zettl group

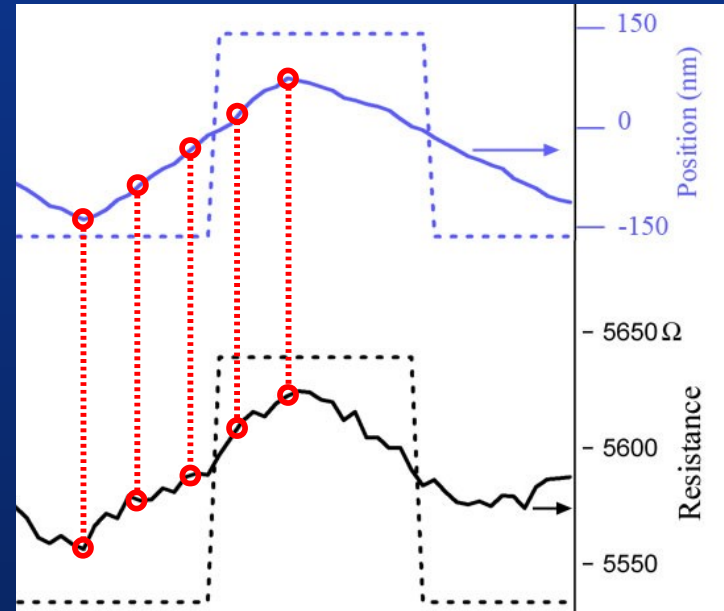
- Preliminary fabrication of Fe@CNT arrays
- Determine mechanism of motion
 - Electromigration, electron wind
- Origin of resistance changes
 - Intershell coupling perturbation
 - Geometry effects (with diffusive transport)
 - Electron resonance effects

Further research

- Multistate devices?

20ns pulses @2V

3nm steps



- Signal enhancement?

Electrode/nanoparticle material

Geometry changes

Fewer nanotube walls



Conclusions

- Stable, sealed mechanism
- Easy to synthesize (initially)
- Easy to read out
 - Electronic, nonperturbative
(TEM just for observation)
- R/W voltages compatible with existing tech.



Acknowledgments

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- Center of Integrated Nanomechanical Systems (COINS)

References:

G.E. Begtrup, W. Gannett, A. Zettl, et al. Nanoscale reversible mass transport for archival memory. *Nano Letters* 9 (5), 1835-1838 (2009).

G.E. Begtrup, W. Gannett, A. Zettl et al. Facets of nanotube synthesis: High-resolution transmission electron microscopy study and density functional theory calculations. *Phys. Rev. B* 79 (20), 205409 (2009).

